

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Thomas A. Figura, Kevin Donohoe, & Thomas Dunbar

Serial No.: 09/470,650

Filed: December 22, 1999

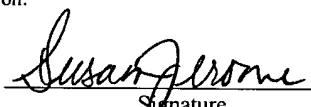
Title: USE OF A PLASMA SOURCE TO FORM A LAYER
DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§
§ Group Art Unit: 2829
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§ Examiner: Lisa Kilday
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§ Atty. Docket: 94-0280.04
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AMENDMENT AND RESPONSE TO THE OFFICE ACTION DATED JUNE 18, 2003

Commissioner for Patents
P.O. Box 1450
Washington, D.C. 20231

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on:	
Date 7/15/03	 Signature

Dear Sir:

Applicants herein respond to the Office Action dated June 8, 2003. Please amend the above-captioned application as follows.

IN THE CLAIMS

Please cancel claims 1-8, 10, 12-14, 19, 23-24, 29-32, and 36-40 without prejudice.

Please amend the claims to the form indicated below.

11. (Once amended) A method of processing a semiconductor device, comprising:
- providing a first protruding feature on a layer of said semiconductor device;
 - providing a second protruding feature on said layer;
 - defining a recess between said first protruding feature and said second protruding feature; and
 - plasma-depositing a material within said recess, wherein said step of plasma-

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